

General Description

The WSD20L120ADN56 is the highest performance trench P-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSD20L120ADN56 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 10	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V}^1$	-88	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V}^1$	-45	A
I_{DM}	Pulsed Drain Current ²	-310	A
EAS	Single Pulse Avalanche Energy ³	80	mJ
I_{AS}	Avalanche Current	-40	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	52	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ ($t \leq 10\text{s}$)	---	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	2.4	$^\circ\text{C/W}$

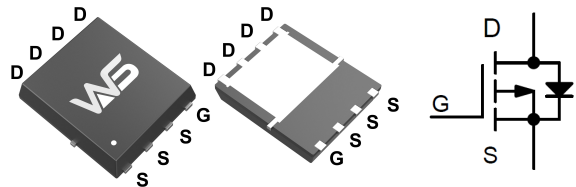
Product Summary

BVDSS	RDSON	ID
-20V	4m Ω	-88A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

DFN5X6-8 Pin Configuration



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=-1mA$	---	-0.0212	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-4.5V, I_D=-20A$	---	4	5	m Ω
		$V_{GS}=-2.5V, I_D=-20A$	---	5.5	7.5	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.4	-0.6	-1.0	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.8	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-20V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-20V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	-6	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V, I_D=-20A$	---	30	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	1.5	2.5	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-10V, V_{GS}=-4.5V, I_D=-20A$	---	32	---	nC
Q_{gs}	Gate-Source Charge		---	8	---	
Q_{gd}	Gate-Drain Charge		---	7	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-10V, V_{GEN}=-4.5V, R_G=3\Omega, I_D=-1A, R_L=0.5\Omega$	---	12	---	ns
T_r	Rise Time		---	10	---	
$T_{d(off)}$	Turn-Off Delay Time		---	85	---	
T_f	Fall Time	$V_{DS}=-10V, V_{GS}=0V, f=1MHz$	---	34	---	pF
C_{iss}	Input Capacitance		---	3350	---	
C_{oss}	Output Capacitance		---	360	---	
C_{rss}	Reverse Transfer Capacitance		---	230	---	

Diode Characteristics

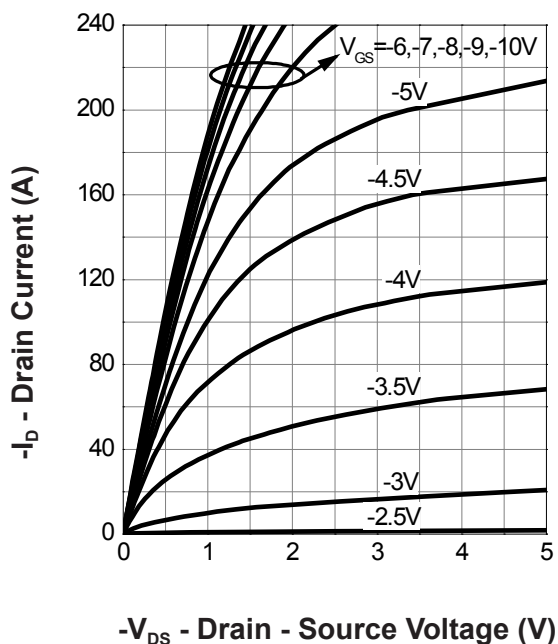
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,6}	$V_G=V_D=0V$, Force Current	---	---	-88	A
I_{SM}	Pulsed Source Current ^{2,6}		---	---	-310	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-15A, dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	30	---	nS
Q_{rr}	Reverse Recovery Charge		---	25	---	nC

Note :

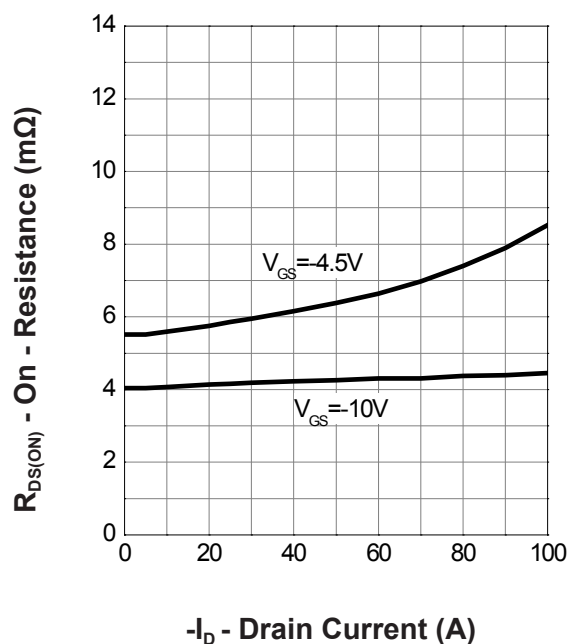
- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, $t<10\text{sec}$.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-10V, V_{GS}=-10V, L=0.1mH, I_{AS}=-40A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Operating Characteristics

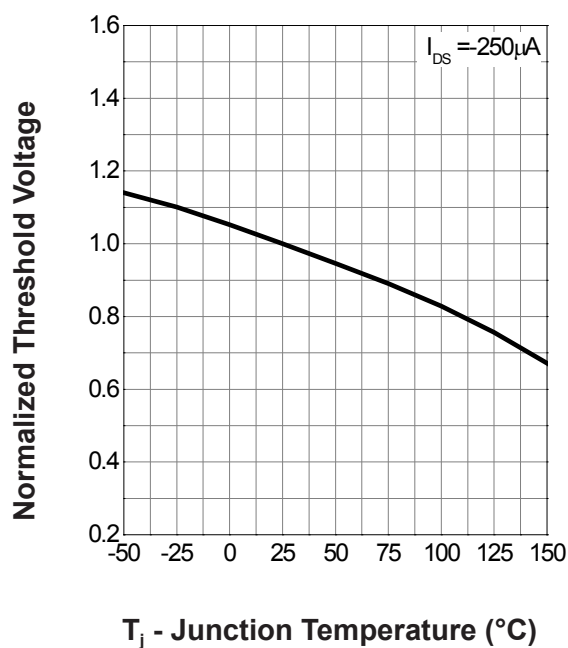
Output Characteristics



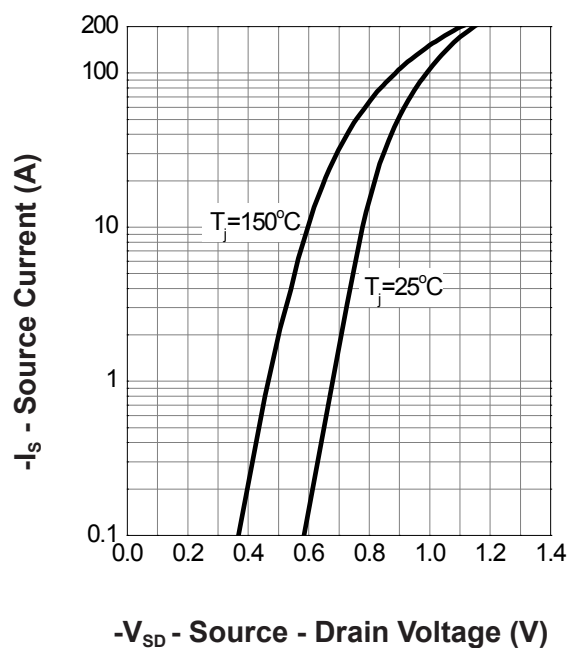
Drain-Source On Resistance



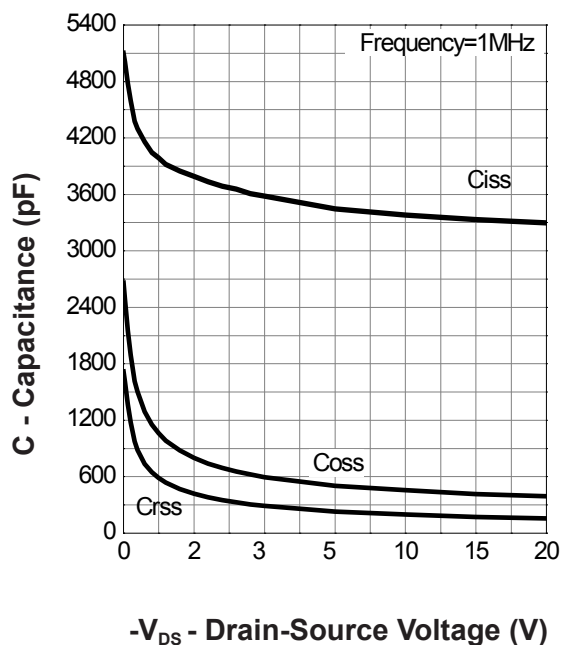
Gate Threshold Voltage



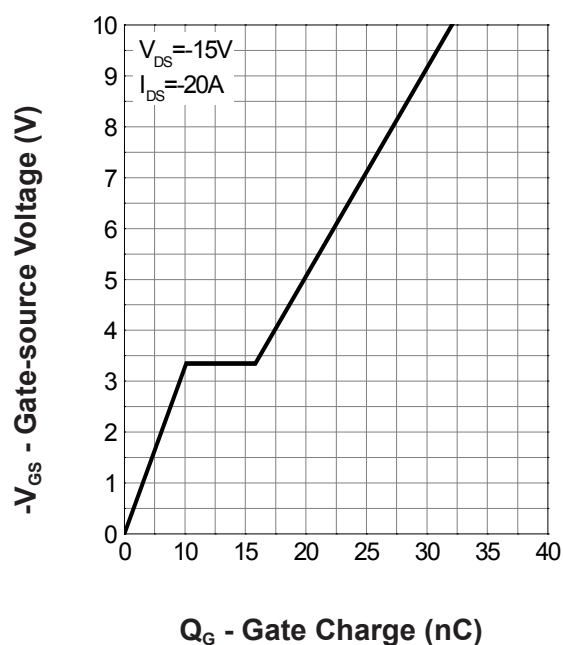
Source-Drain Diode Forward



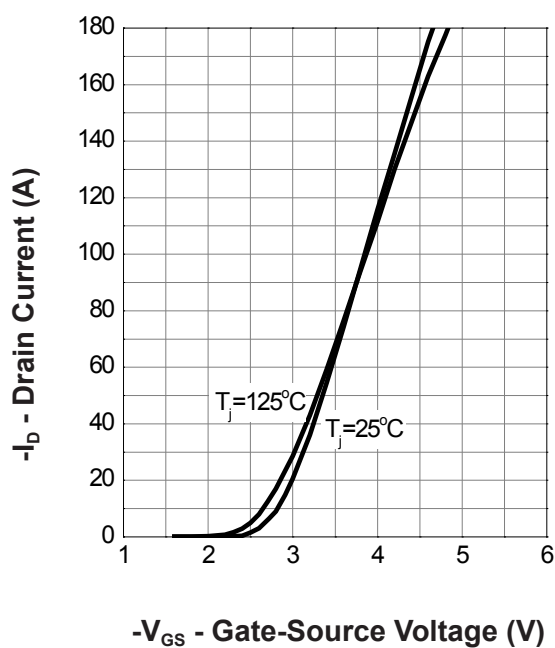
Capacitance



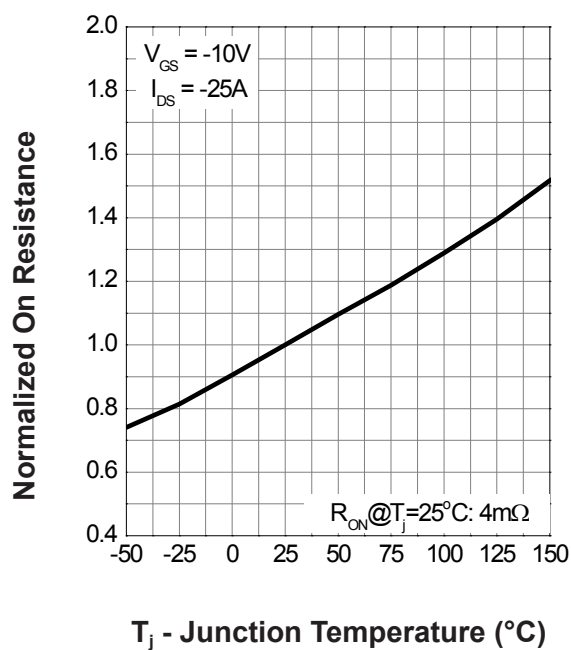
Gate Charge



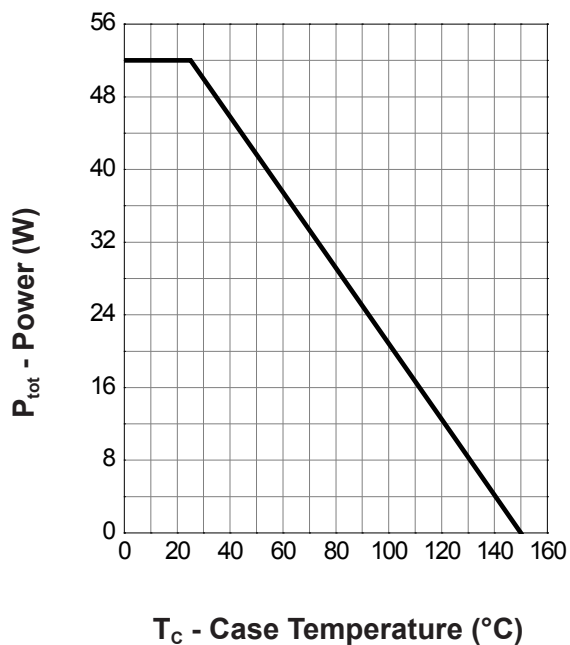
Transfer Characteristics



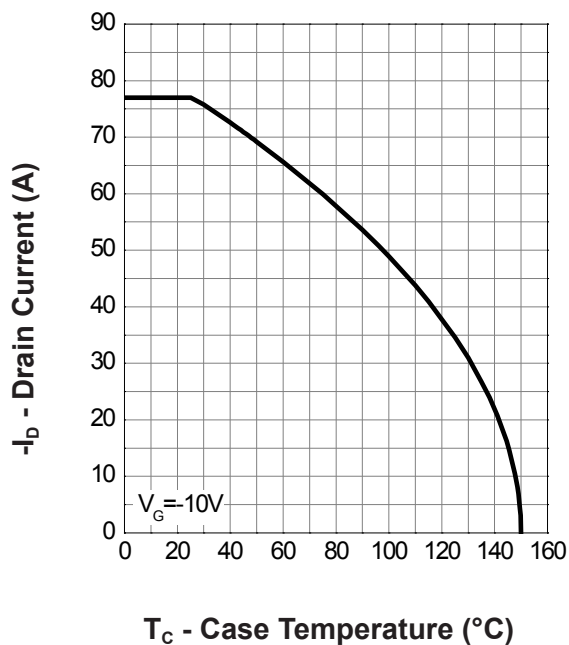
Drain-Source On Resistance



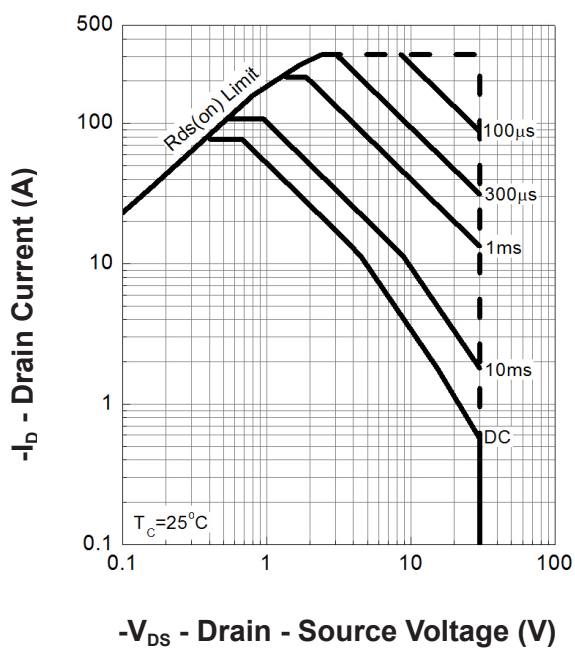
Power Dissipation



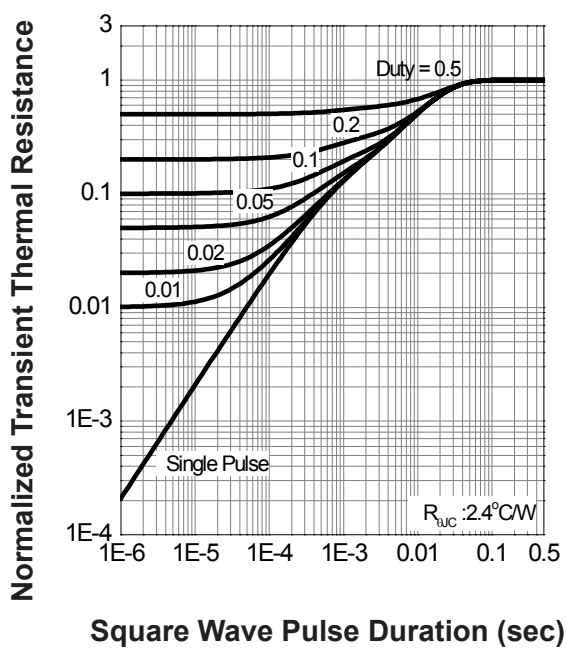
Drain Current



Safe Operation Area



Thermal Transient Impedance



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